EECS151/251A
Spring 2021
Digital Design and Integrated Circuits

Instructor:

John Wawrzynek

Lecture 24:

Clocks, Packaging, and Power Distribution

Announcements

- ❑ Virtual Front Row for today 4/20:
  - ❑ *Jose Rodriguez*
  - ❑ *Rahul Arya*
  - ❑ *Zitao Fang*
  - ❑ *Jeremy Ferguson*
- ❑ **Please ask question or make comments!**
- ❑ Homework assignment 10 posted - due next Monday.
- ❑ HW 11 - final problem set - posted end of this week.

Announcements

❑ End game:

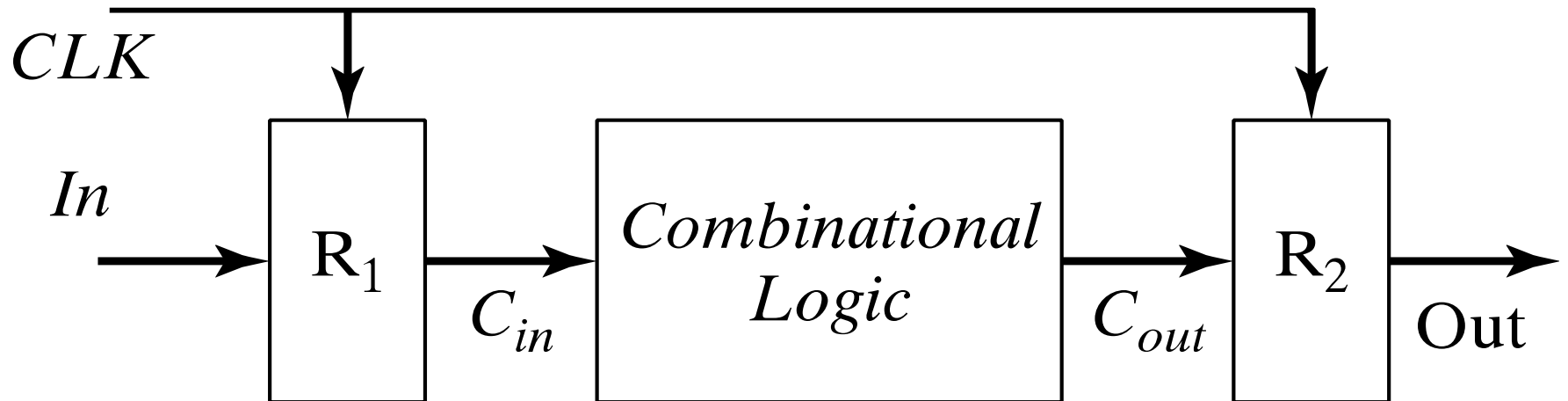| 14	4/20	Clock and Power Distribution		Checkpoint 2 due, , Checkpoint 3 & 4 Released	
	4/22	Testing, Faults, Error Correction Codes			
15	4/27	Inside Logic Synthesis Tools		Checkpoint 3 due	
	4/29	Wrap-up and Exam Review			
16	5/5	RRR No Lecture		Checkpoint 4	Final Checkoff due
	5/7	RRR No Lecture			
FINAL	5/14	No Class – Final Exam 7-10 PM			

Outline

- ❑ Clock non-idealities
- ❑ Clock Distribution
- ❑ Chip packaging
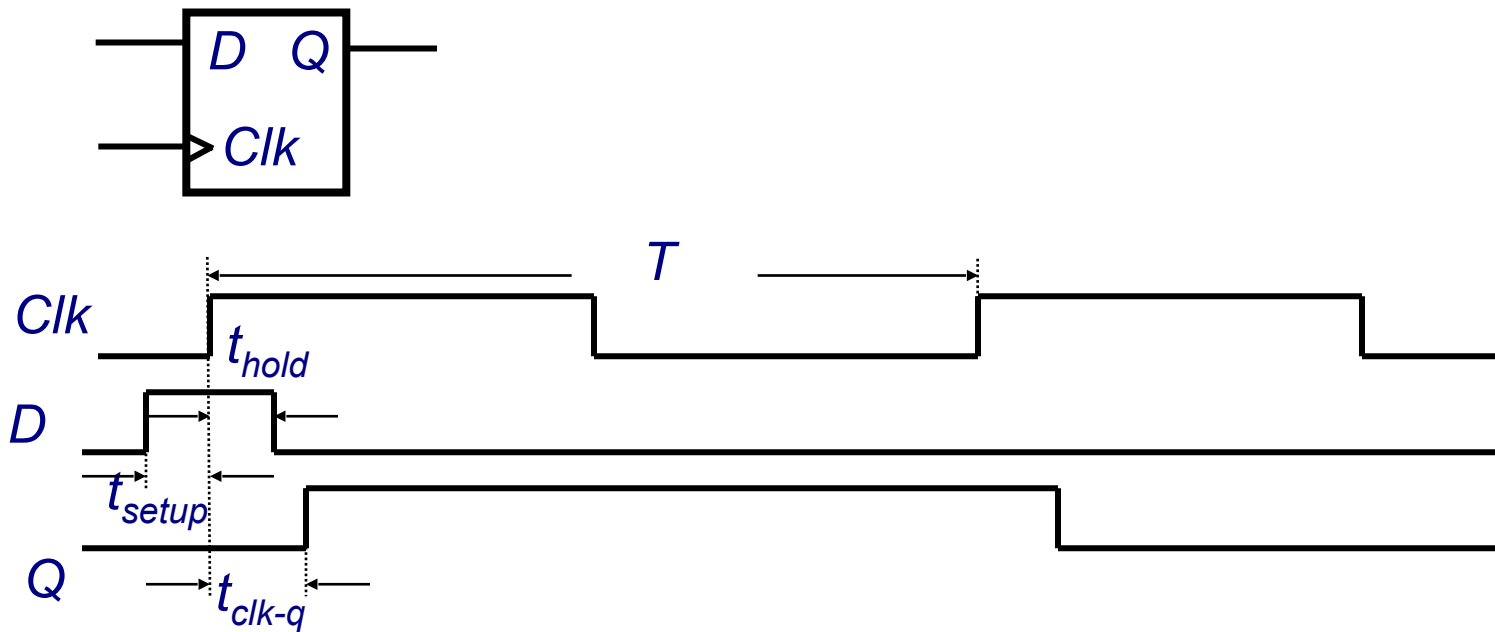- ❑ Power Distribution

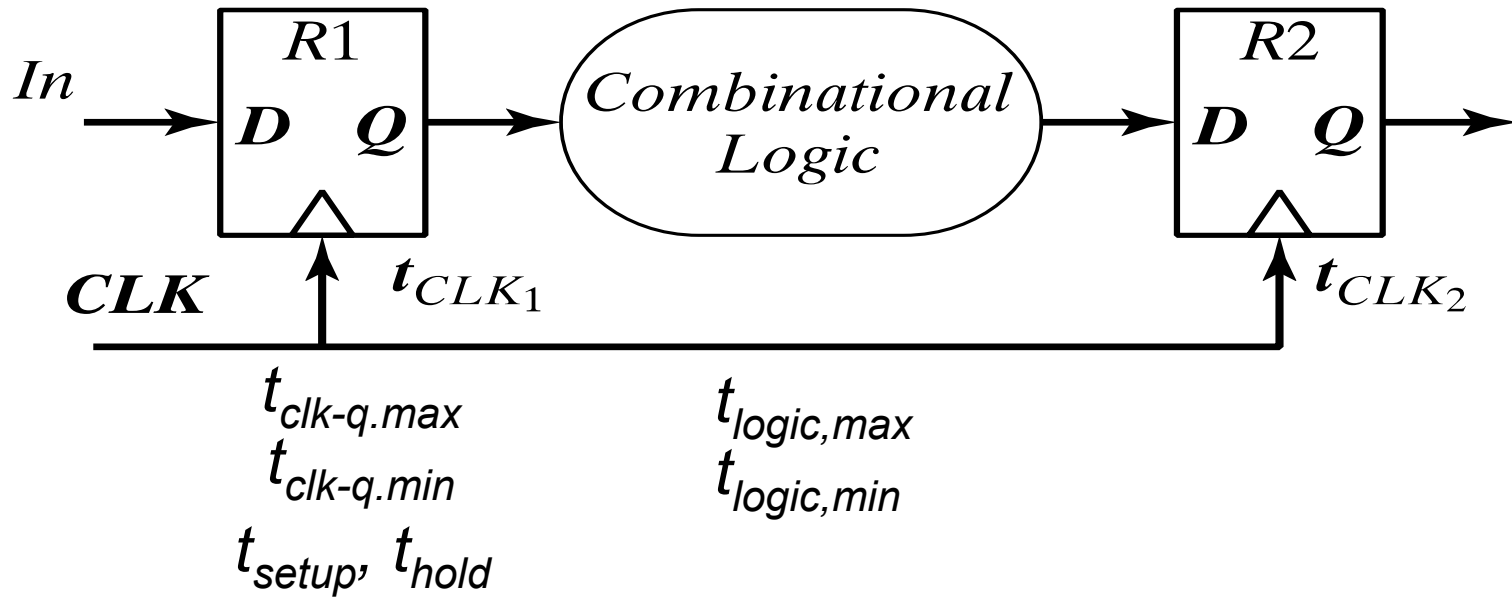# Synchronous Timing - Review

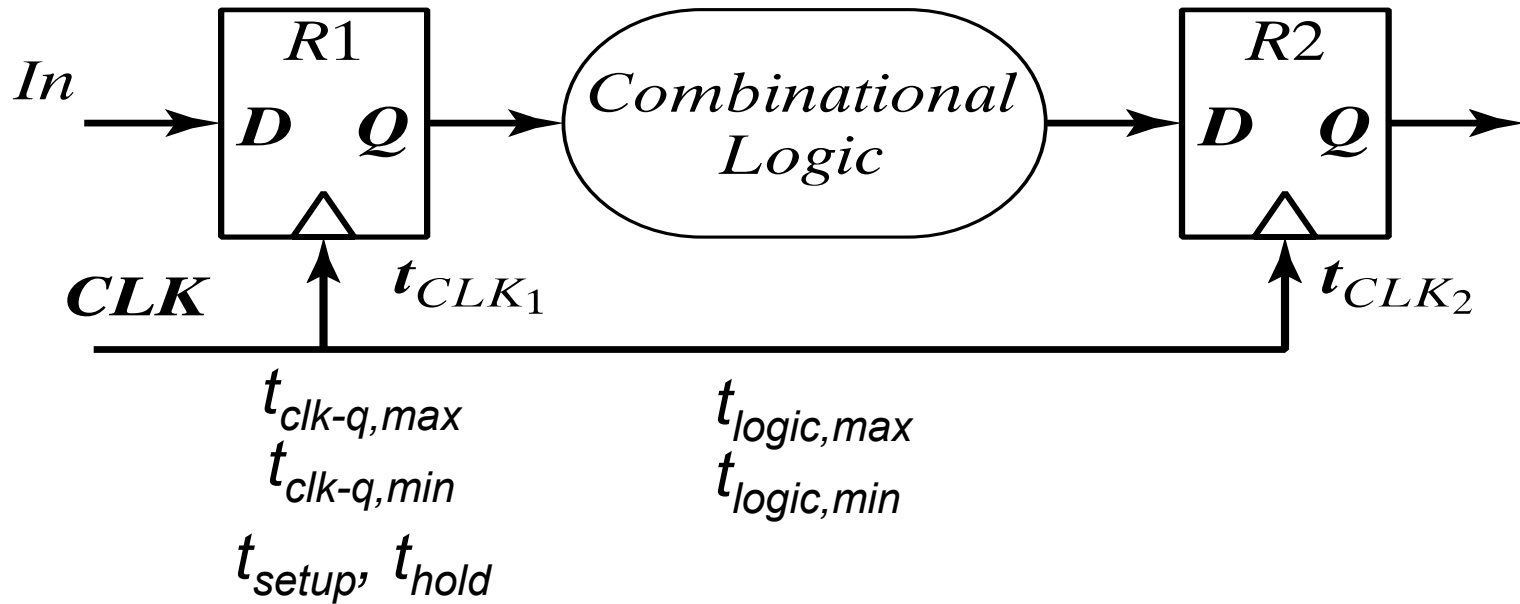# *Synchronous Timing*

Register Timing Parameters

Output delays can be different for rising and falling data transitions

Timing Constraints

Timing Constraints

Cycle time (max): $T_{Clk} > t_{clk-q,max} + t_{logic,max} + t_{setup}$

Race margin (min): $t_{hold} < t_{clk-q,min} + t_{logic,min}$

Clock Nonidealities

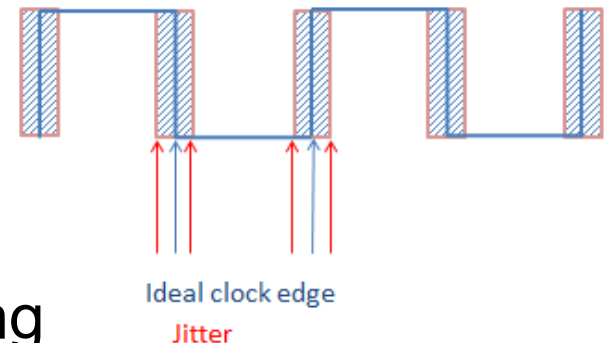# *Clock Nonidealities*

❑ **Clock skew: t_{SK}**

  ▪ Time difference between the sink (receiving) and source (launching) clock edge; deterministic + random

❑ **Clock jitter**

  ▪ Temporal variations in consecutive edges of the clock signal; modulation + random noise

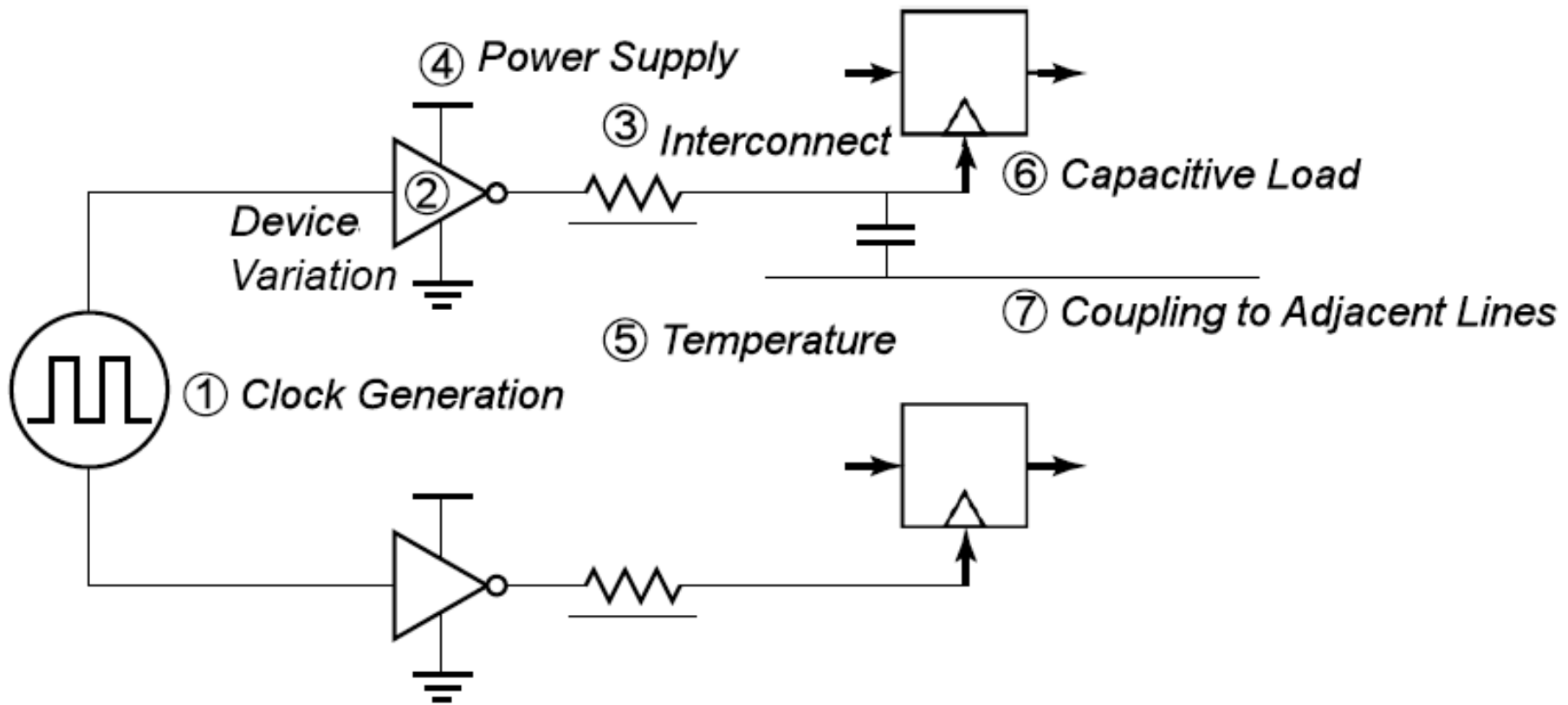 ▪ Cycle-to-cycle (short-term) t_{JS}

  ▪ Long term t_{JL}

❑ **Variation of the pulse width**

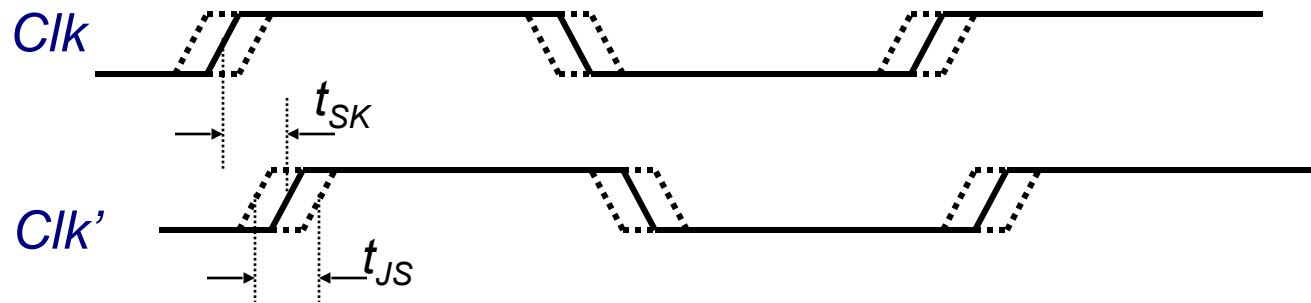 ▪ Important for level sensitive clocking

Ideal clock edge

Jitter

Clock Uncertainties

Sources of clock uncertainty

Clock Skew and Jitter

Clk

Clk'

t_{SK}

t_{JS}
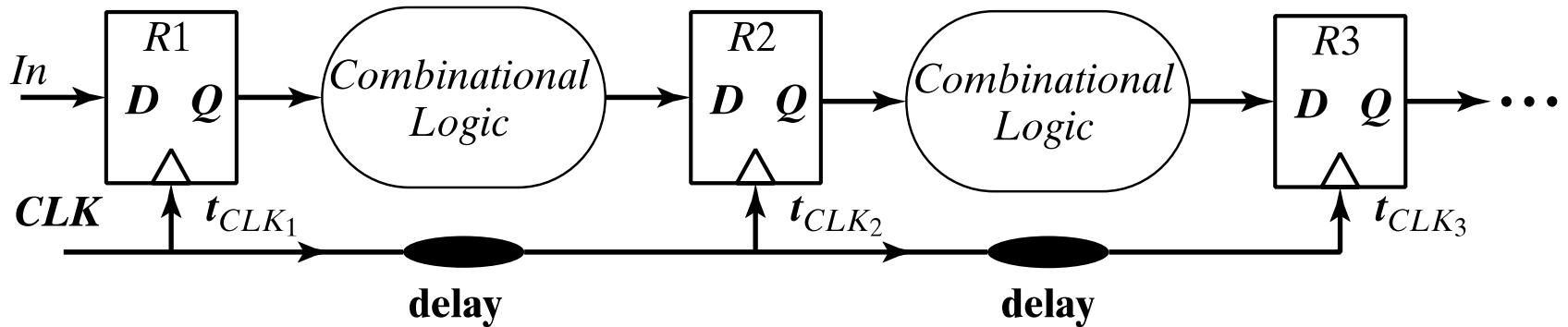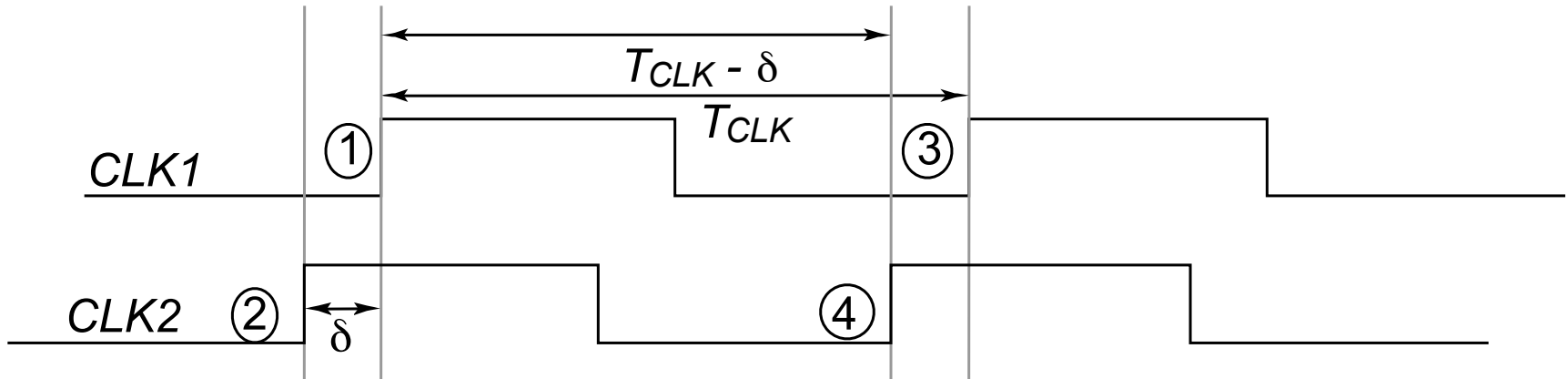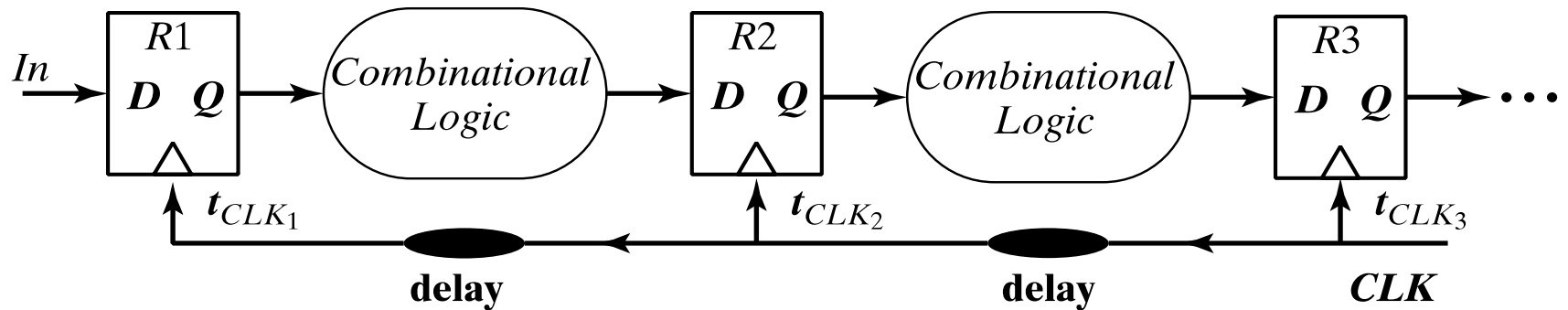
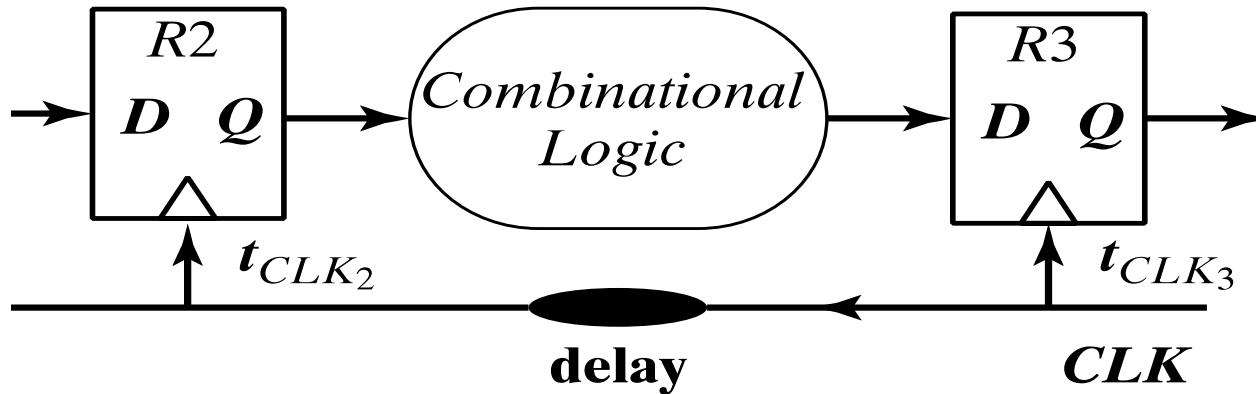❑ Both skew and jitter affect the effective cycle time and the race margin

Positive Skew

Launching edge arrives before the receiving edge

Negative Skew

Receiving edge arrives before the launching edge

Timing Constraints

R2 D Q → *Combinational Logic* → R3 D Q

t_{CLK_2}

delay

t_{CLK_3}

CLK

$t_{clk\text{-}q,max}$
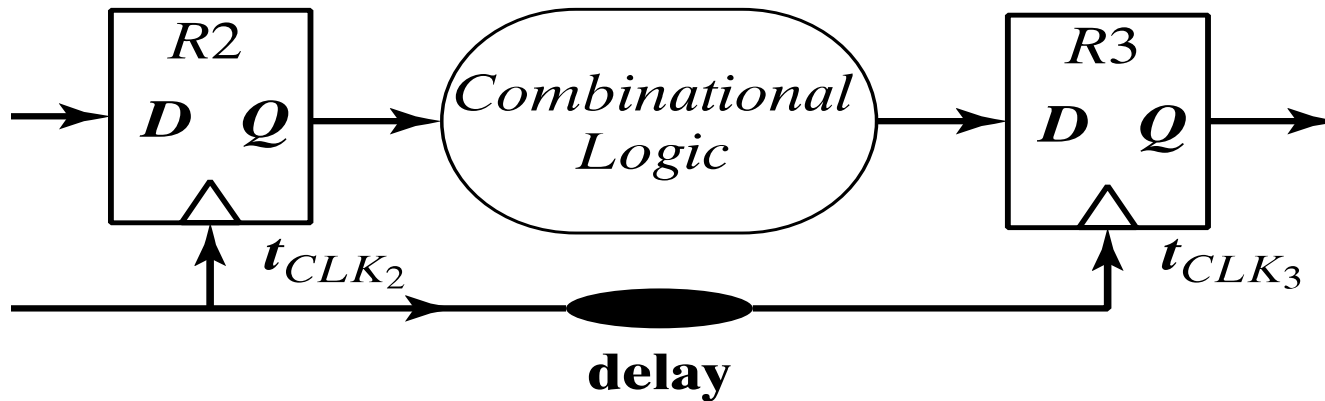$t_{clk\text{-}q,min}$
t_{setup}, t_{hold}

$t_{logic,max}$
$t_{logic,min}$

Minimum cycle time:

$T_{clk} + \delta = t_{clk\text{-}q,max} + t_{setup} + t_{logic,max}$

Skew may be negative or positive

Timing Constraints
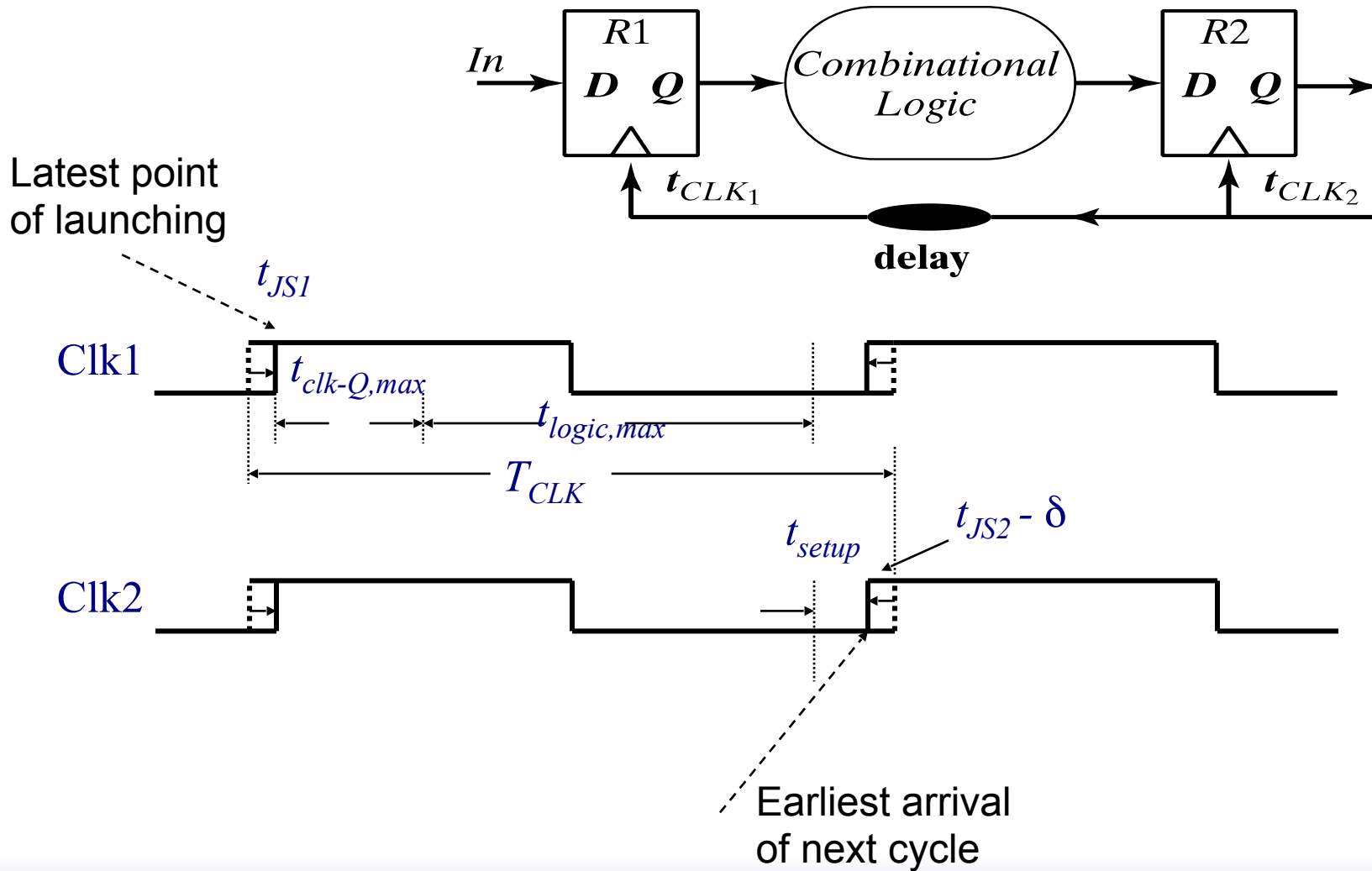

$t_{clk-q,max}$
$t_{clk-q,min}$
t_{setup}, t_{hold}

$t_{logic,max}$
$t_{logic,min}$

Hold time constraint:

$t_{(clk-q,min)} + t_{(logic,min)} > t_{hold} + \delta$

Skew may be negative or positive

Jitter Contributes to Critical Path

Clock Constraints in Edge-Triggered Systems

If launching edge is late and receiving edge is early, the data will not be too late if:

$$t_{clk\text{-}q,max} + t_{logic,max} + t_{setup} < T_{CLK} - t_{JS,1} - t_{JS,2} + \delta$$
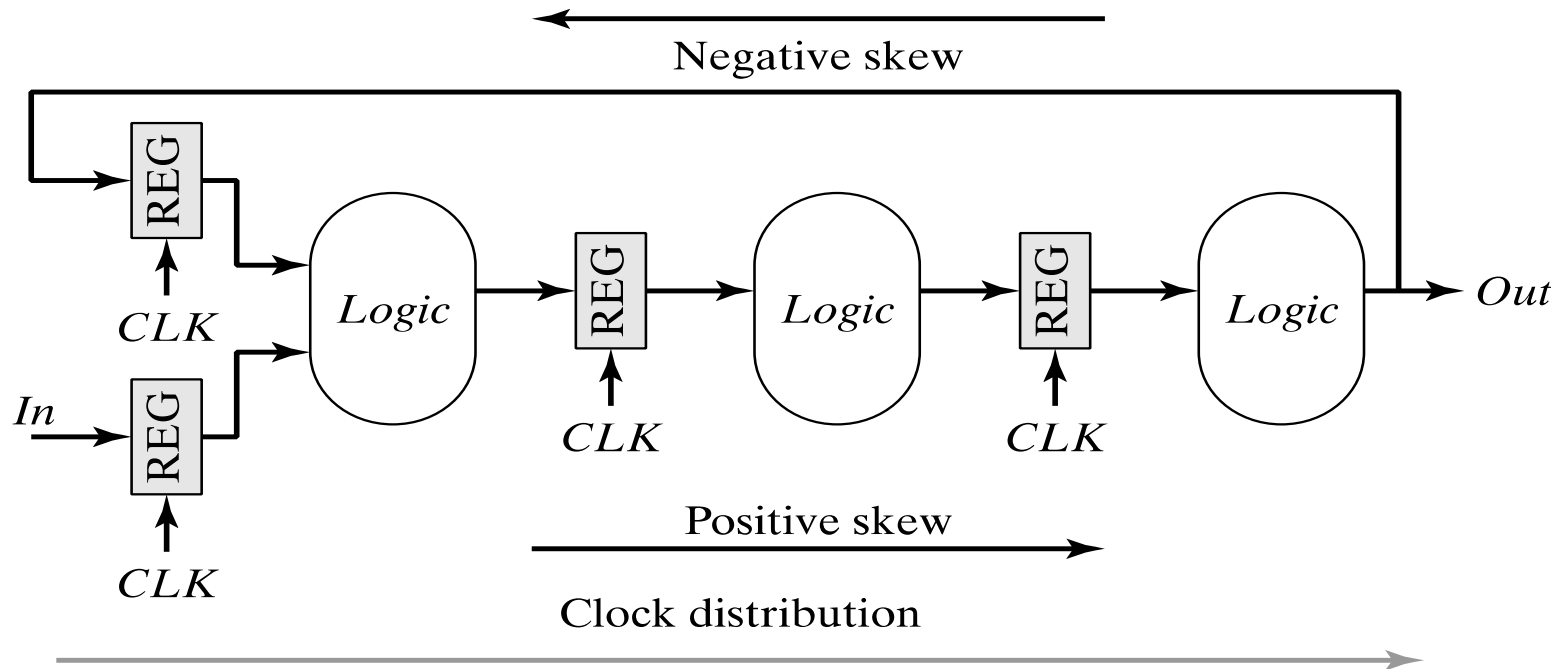
Minimum cycle time is determined by the maximum delays through the logic

$$t_{clk\text{-}q,max} + t_{logic,max} + t_{setup} - \delta + 2t_{JS} < T_{CLK}$$

Skew can be either positive or negative

Jitter t_{JS} usually expressed as peak-to-peak or n x RMS value
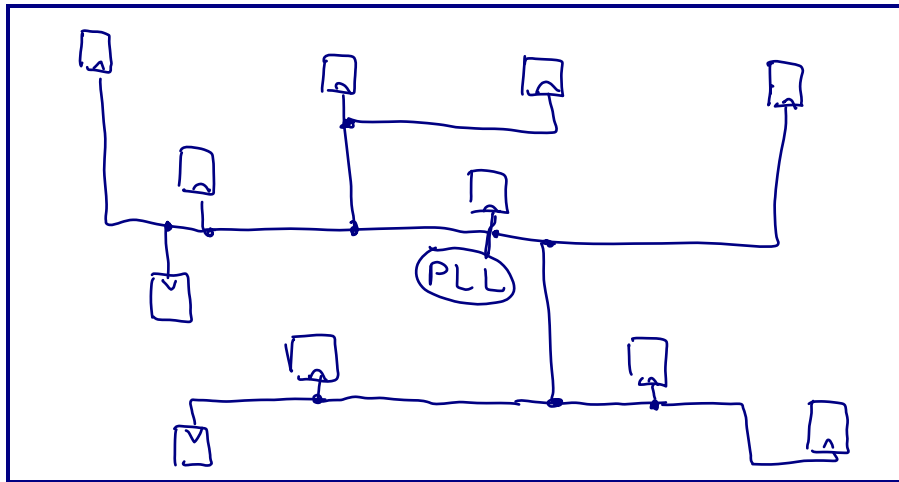
Datapath with Feedback
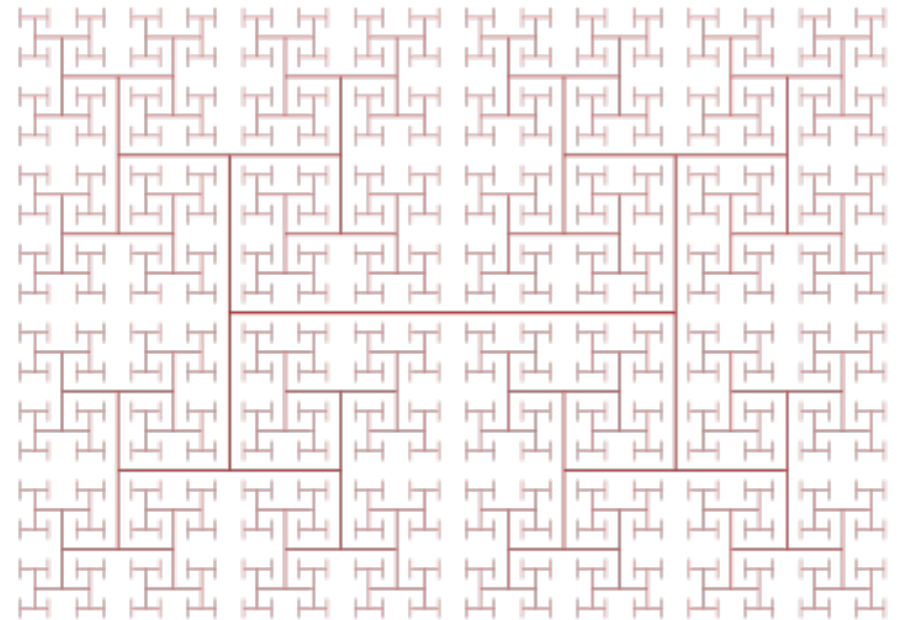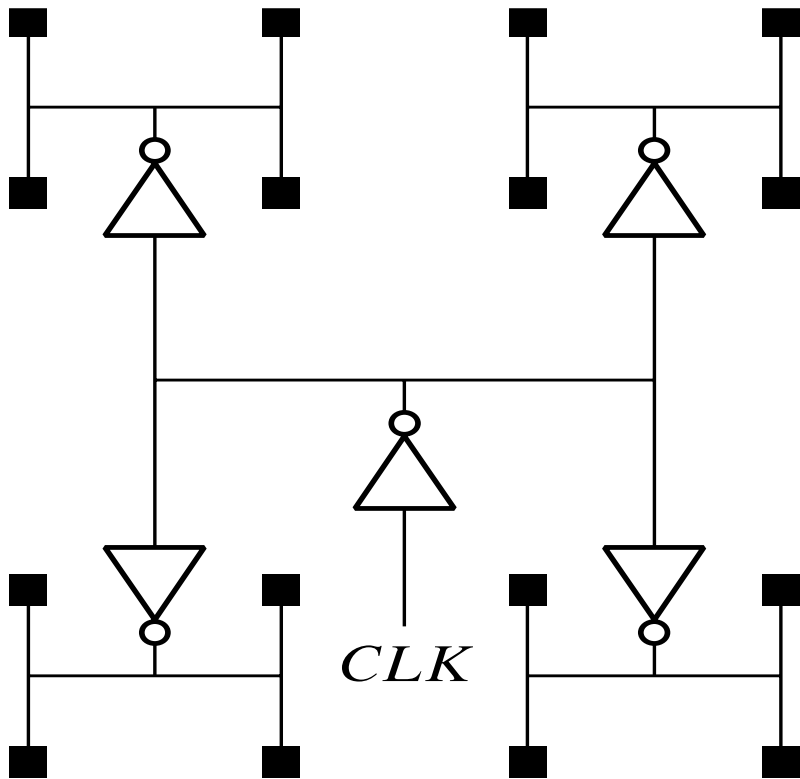
Clock Distribution

Clock Distribution

❑ Single clock generally used to synchronize all logic on the same chip (or region of chip)

  ▪ Need to distribute clock over the entire region

  ▪ While maintaining low skew/jitter

  ▪ And without burning too much power

Clock Distribution

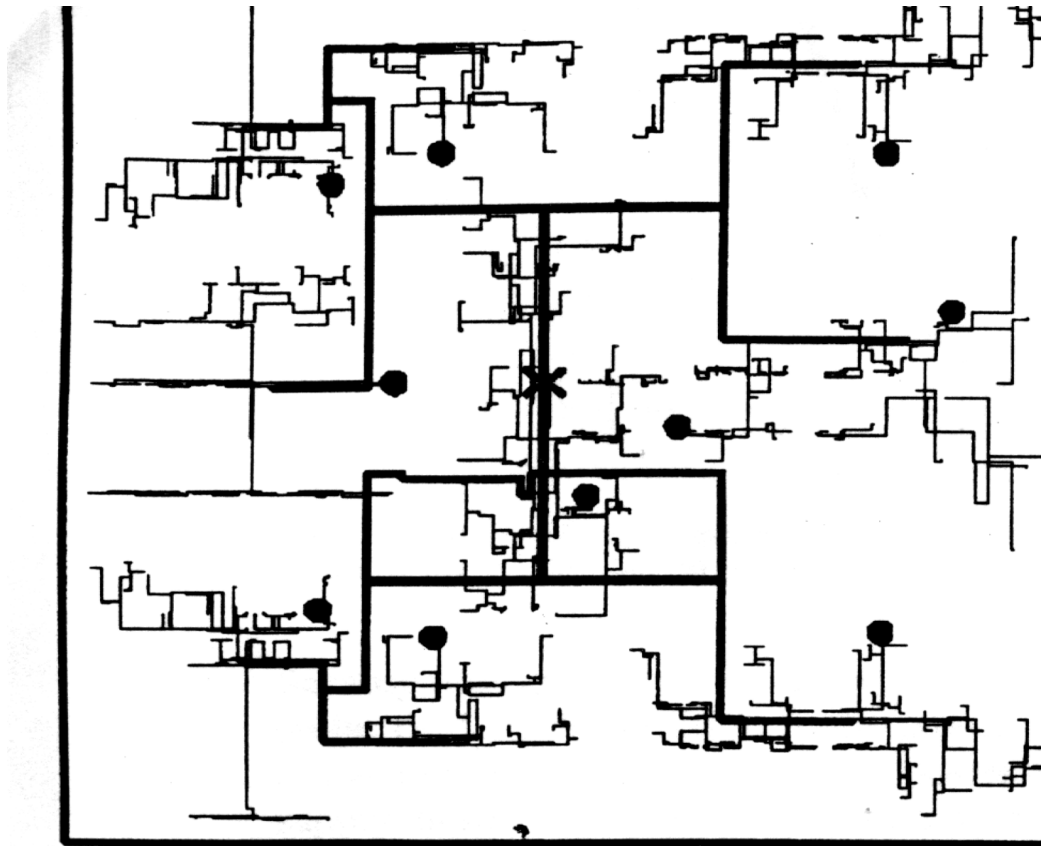❑ What's wrong with just routing wires to every point that needs a clock?
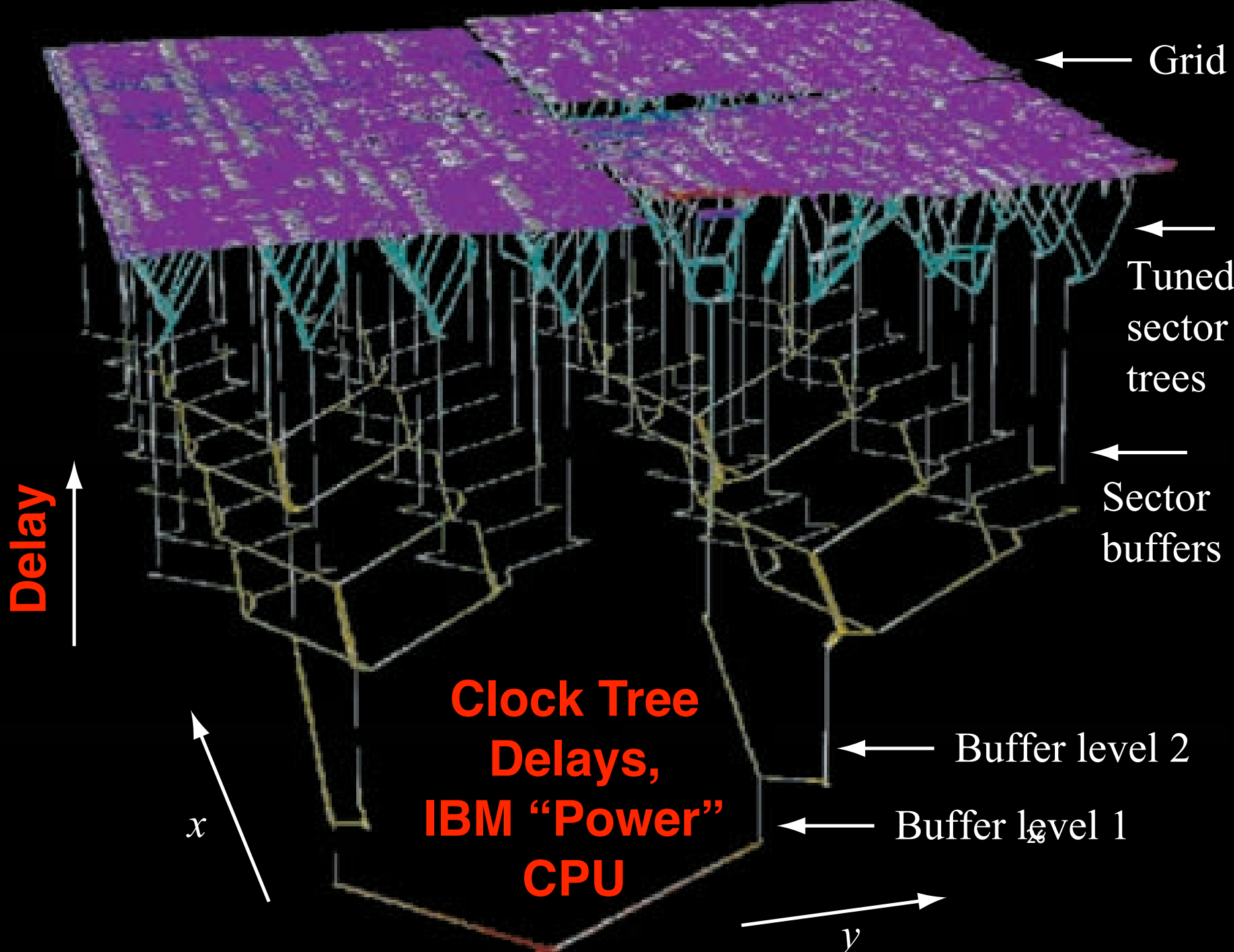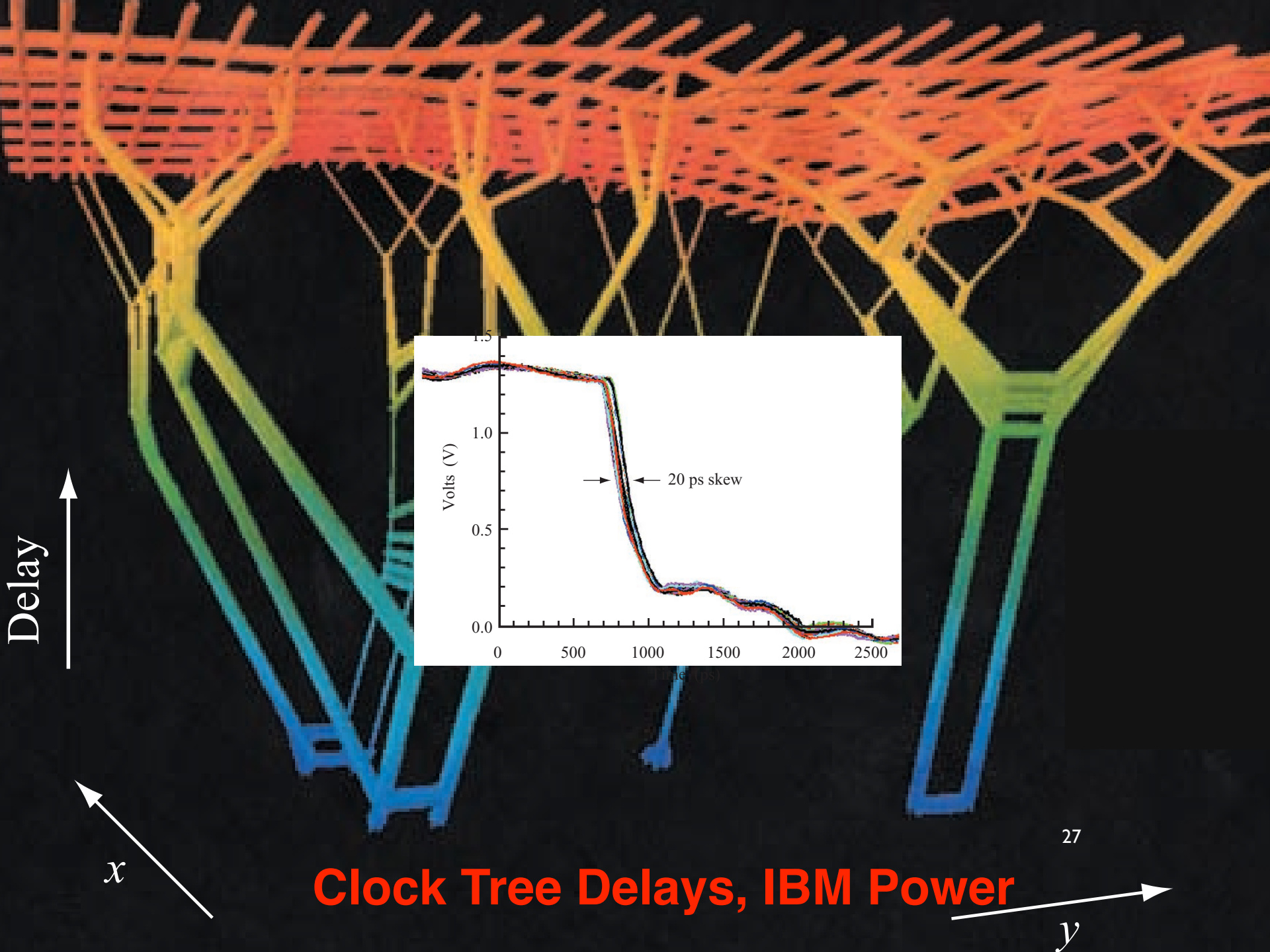
H-Tree

CLK

Equal wire length/number of buffers to get to every location

More realistic ASIC H-tree

[Restle98]

Grid

Tuned sector trees

Sector buffers

Delay

Clock Tree Delays, IBM "Power" CPU

Buffer level 2

Buffer level 1

x

y

Delay

x

y

20 ps skew

Volts (V)

1.5

1.0

0.5

0.0

0   500   1000   1500   2000   2500

Time (ps)

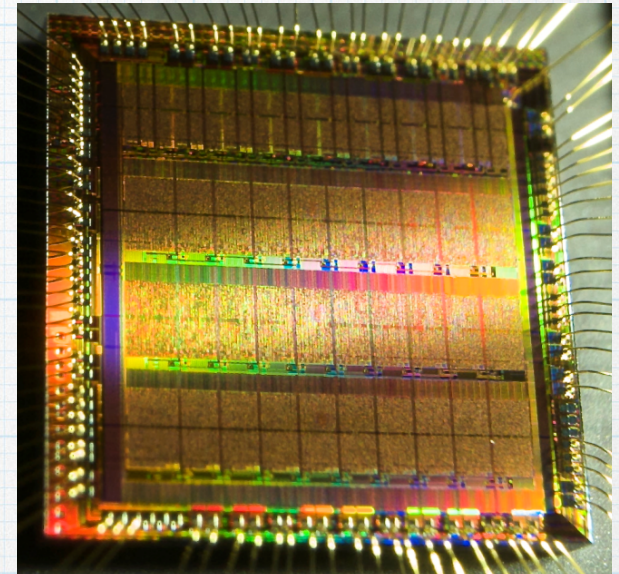**Clock Tree Delays, IBM Power**

Chip Packaging

Chip Packaging

Bonding wire · Chip · Mounting cavity · Lead frame · Pin · L · L'
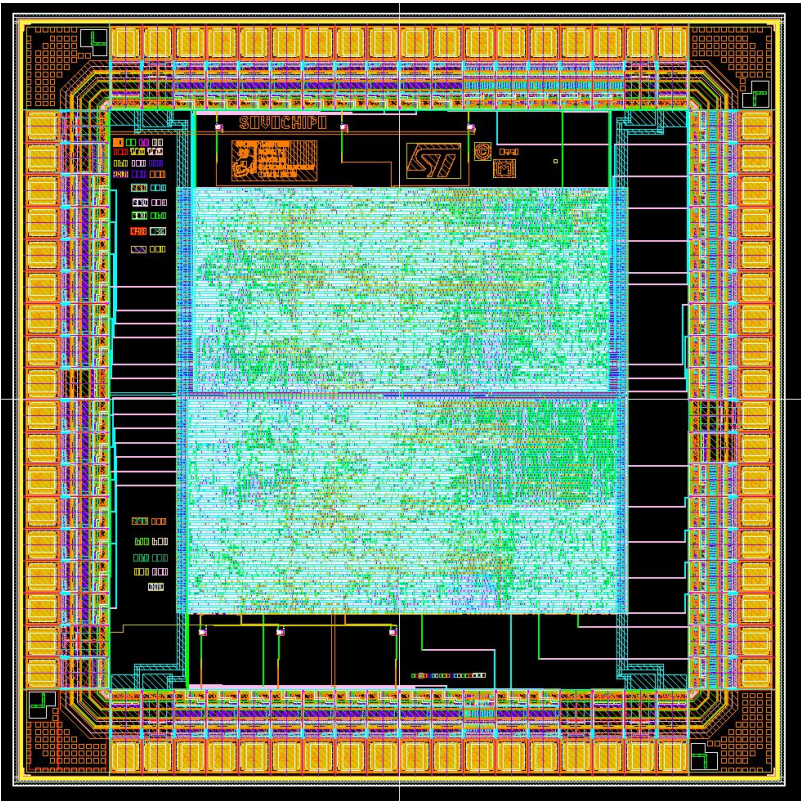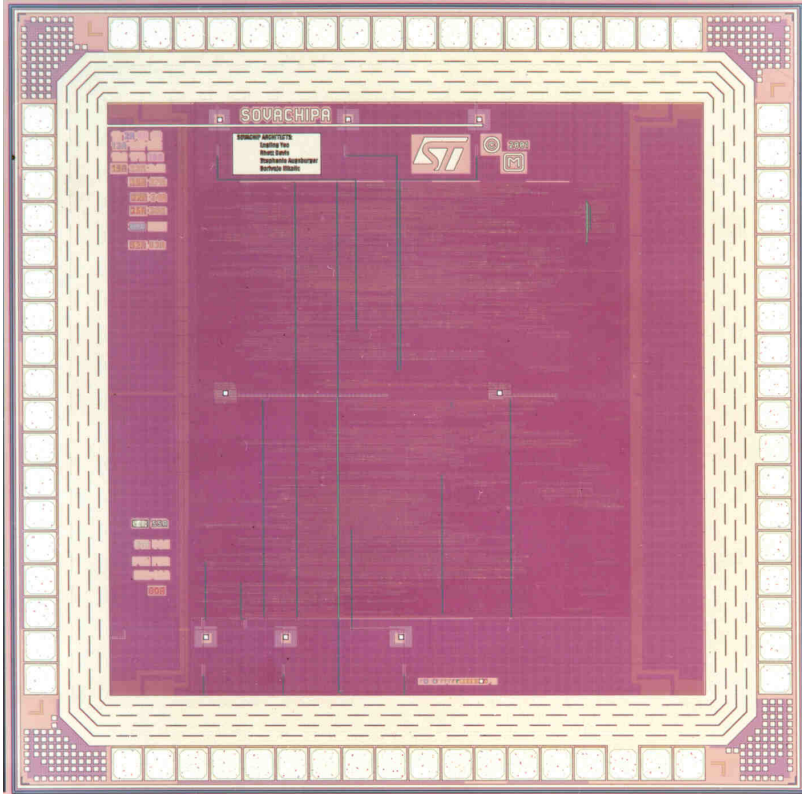
- Bond wires (~25μm) are used to connect the package to the chip

- Pads are arranged in a frame around the chip

- Pads are relatively large

  - ~100μm in 0.25μm technology, with 100μm pitch

  - 60μm x 80μm at 80μm pitch in 45nm

- Many chips are 'pad limited'

Pad Frame

Layout

Die Photo

Chip Packaging

NAMICS Technology

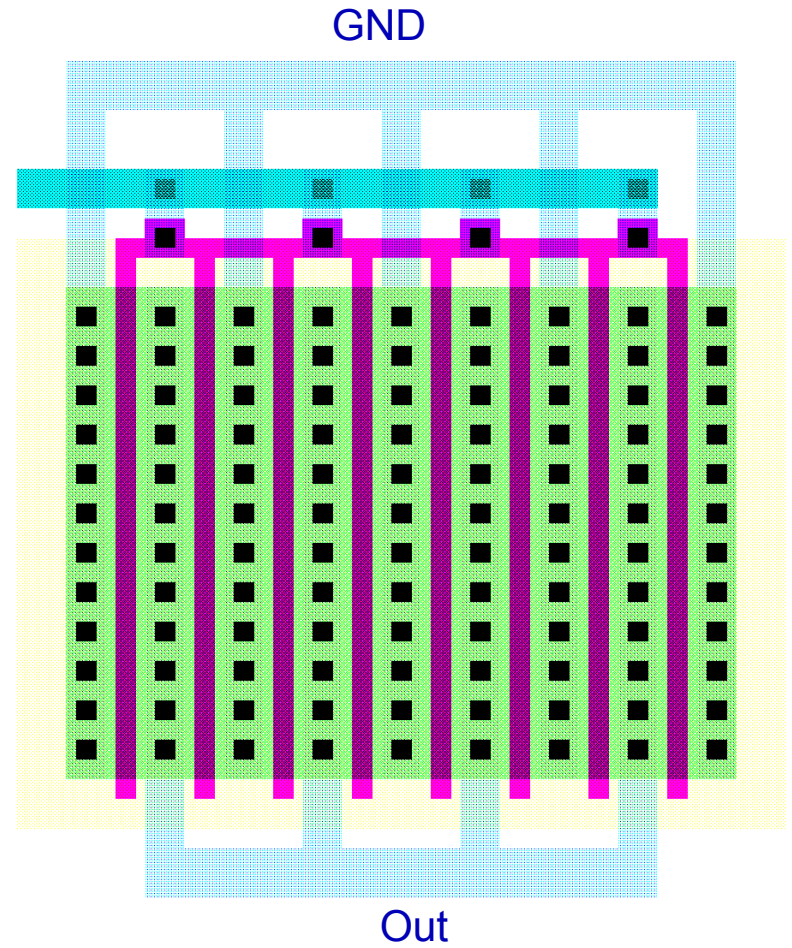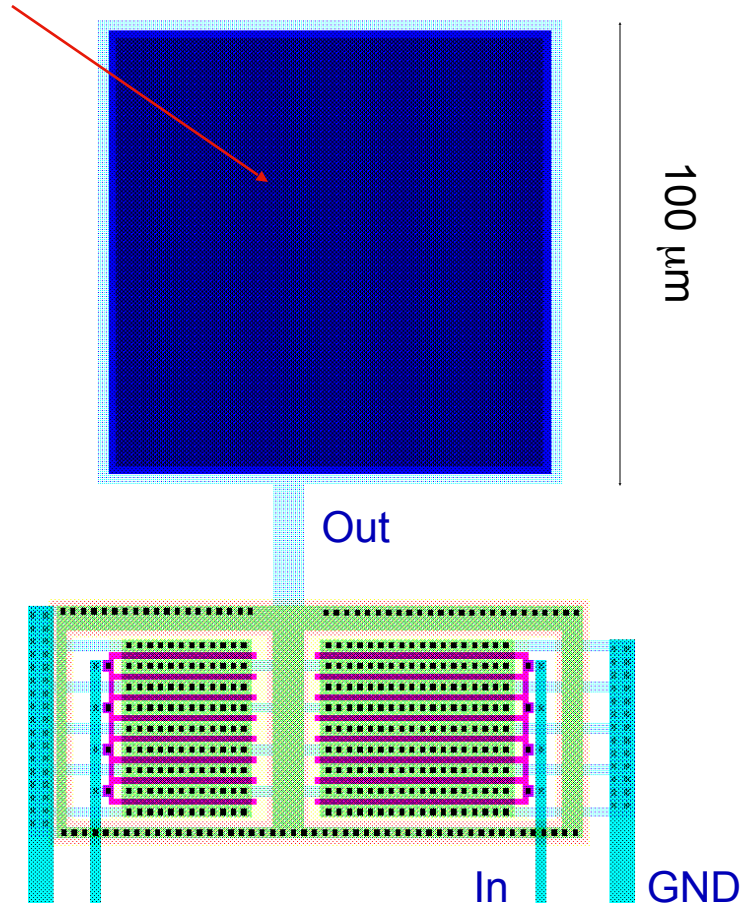Flip-chip solder bumps · Chip · Solder balls · Ceramic base · Board

(b) Ball grid array packaging

▸ An alternative is 'flip-chip':

  ▸ Pads are distributed around the chip

  ▸ The solder balls are placed on pads

  ▸ The chip is 'flipped' onto the package

  ▸ Pads still large
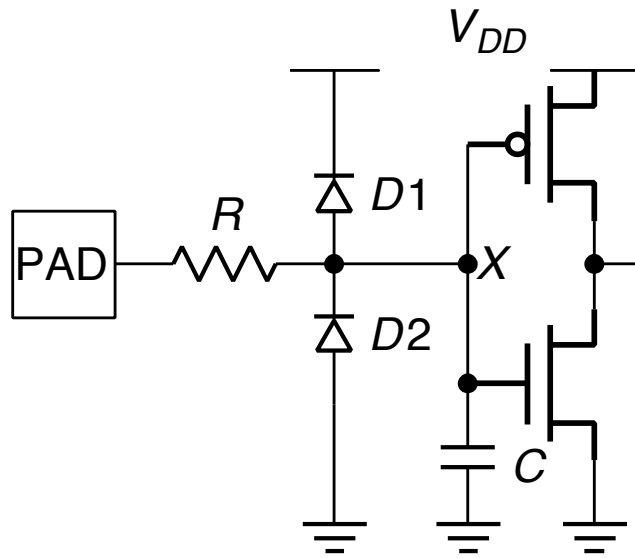
    ▸ But can have many more of them

Bonding Pad Design

Bonding Pad

100 μm

Out

V_DD

In   GND

GND

Out

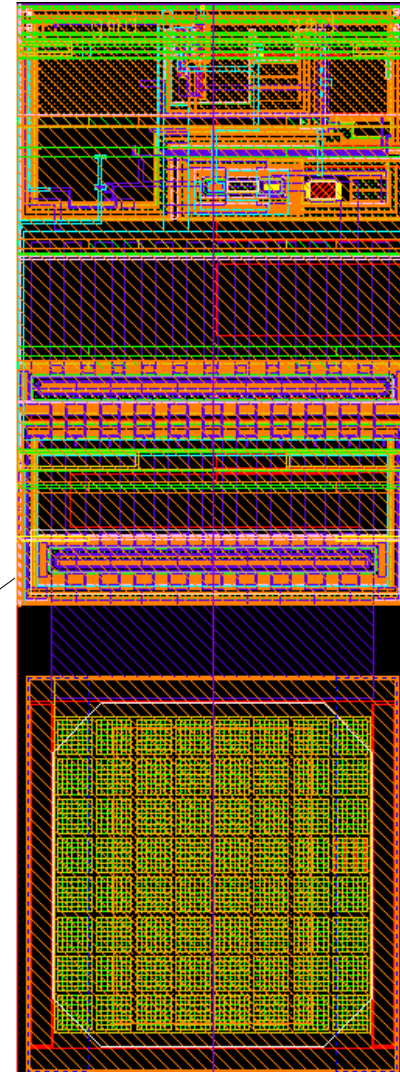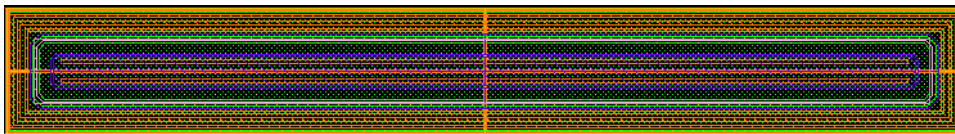# ESD Protection

▸ When a chip is connected to a board or otherwise handled, there is unknown (potentially large) static voltage difference (a few kV)

▸ Equalizing potentials requires (large) charge flow through the pads

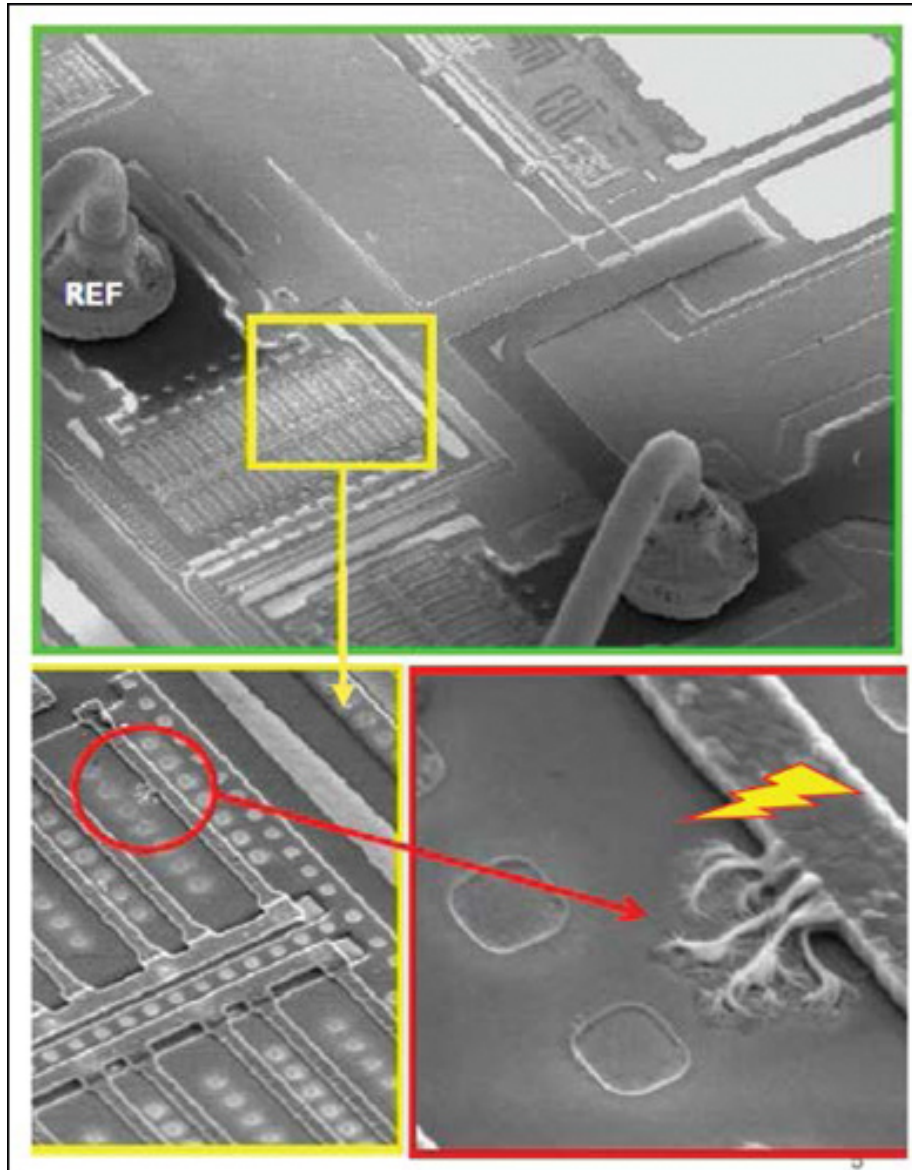▸ Diodes sink this charge into the substrate – need guard rings to pick it up.

Pads + ESD Protection

Diode

When Things Go Bad

[Maxim]

Power Distribution

Power Supply Distribution Issues

▸ **IR drops**

  ▸ Voltage drops due to resistance is power wires

    ▸ *Slower circuits, false switching*

▸ **Metal Migration (electromigration)**

    ▸ *chip failures*

▸ **Inductive Effects**

  ▸ bounce and oscillations on power nodes

All effects are helped by *shorter thicker wires*. Modern processes have special thick metal layers dedicated to power distribution. Area pads help keep connections to package short and distance from pad to circuit short.

Power Delivery

Integrated Circuit Chip — Chip Bumps — Substrate — Printed Conductor Runs

▸ Achieving good reliable power delivery requires a lot of resources:

  ▸ ~70% of package pins just for power

  ▸ Top 2-3 (thick) metal layers

Chip Metal Layers

All effects are helped by *shorter thicker wires*. Modern processes have special thick metal layers dedicated to power distribution. Area pads help keep connections to package short and distance from pad to circuit short.
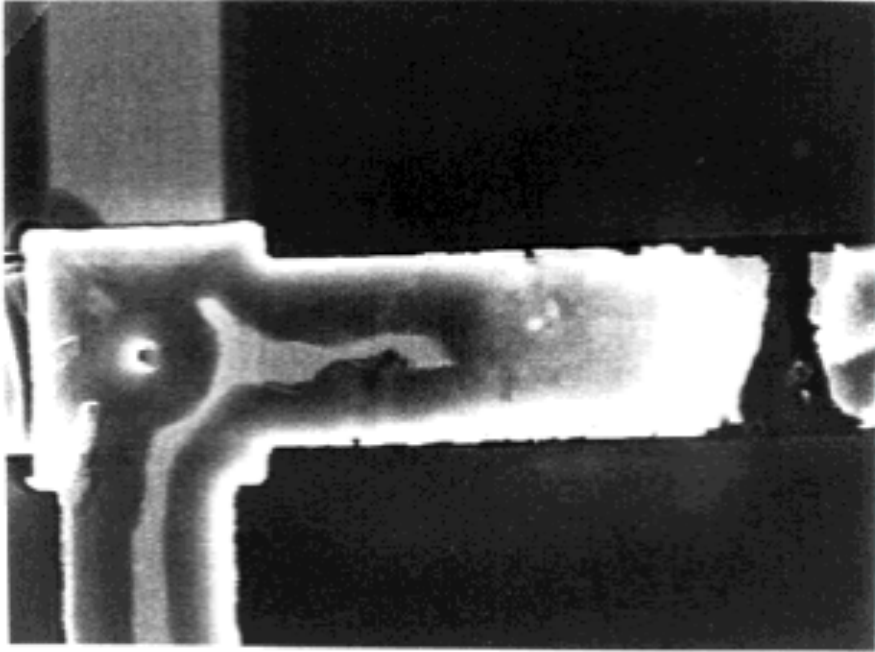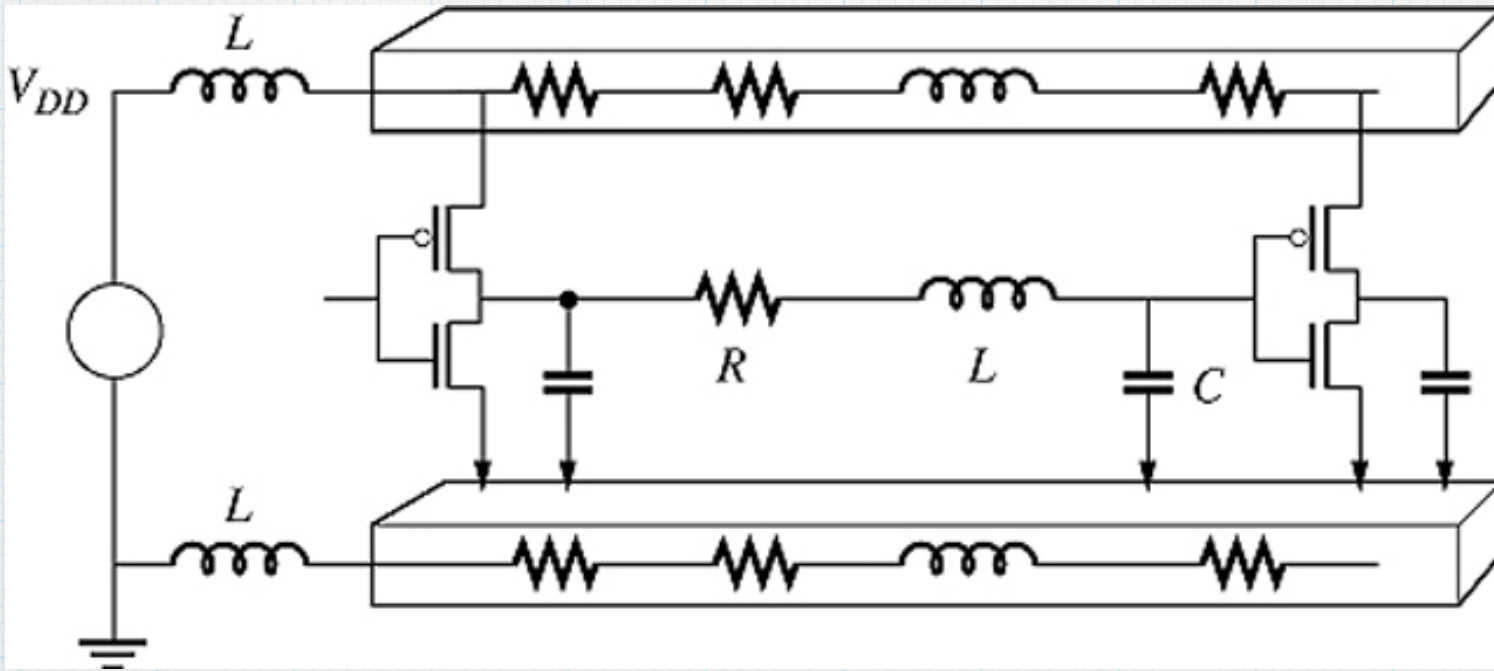
Electromigration

❑ If current density is too high - wires melts

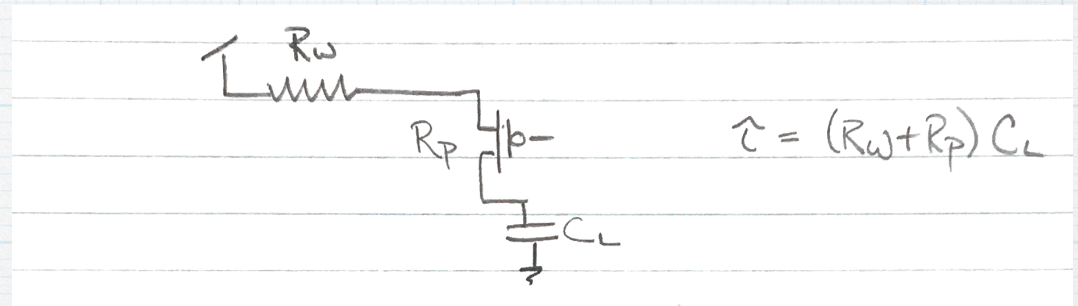❑ "On-chip wires: current limited to ~1mA/μm for 5-7 year lifetime

Power Supply Impedance (Z)

▸ Two principal elements increase Z:

  ▸ Resistance of supply lines (IR drop)
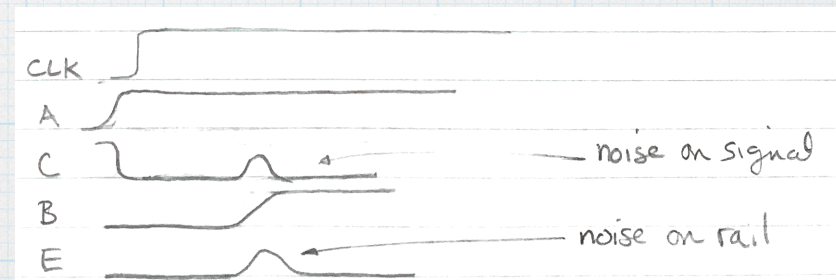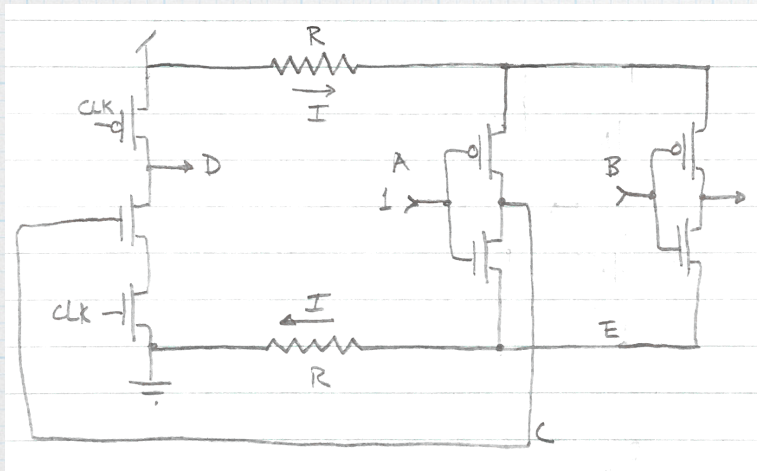
  ▸ Inductance of supply lines (L·di/dt drop)

Power Supply Impedance

▸ IR voltage drop

▸ Slower circuit operation because of series resistance with transistors:

$$\hat{\tau} = (R_W + R_P) C_L$$

▸ IR drops generate "noise":

Scaling and Supply Impedance

▸ Typical target for supply impedance is to get 5-10% voltage variation of nominal supply (e.g., 100mV for 1V supply)

Impedance Requirements of
High-Performance Processors

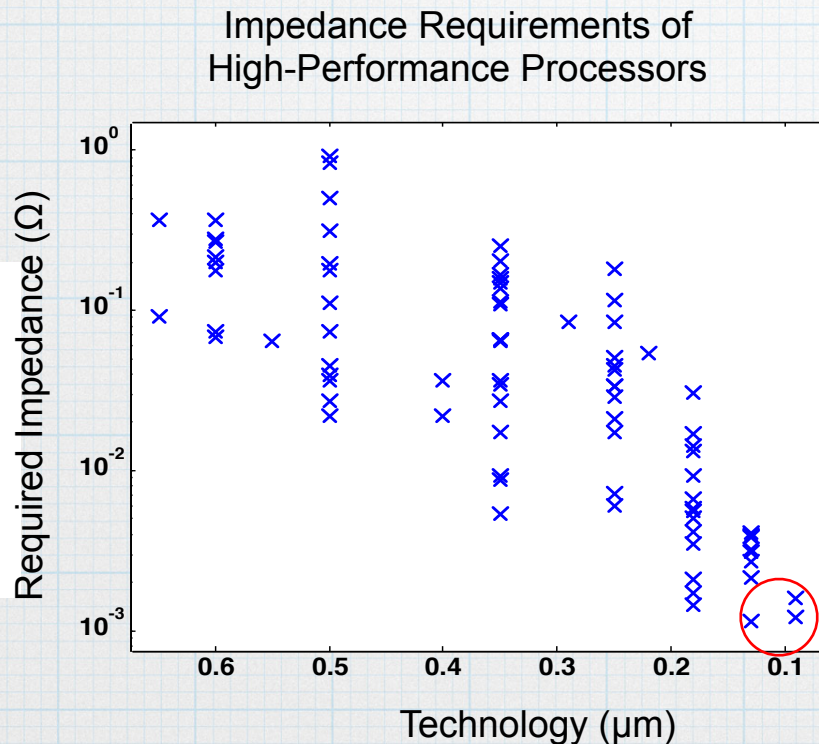❑ In traditional scaling V_{dd} drops while power stays constant.

❑ This forced drastic drop in required supply impedance:

- $V_{dd} \downarrow$, $I_{dd} \uparrow \rightarrow$ $|Z_{required}| \downarrow\downarrow$

❑ Extreme example:

- Vdd = 1V, P=100W => Idd=100A
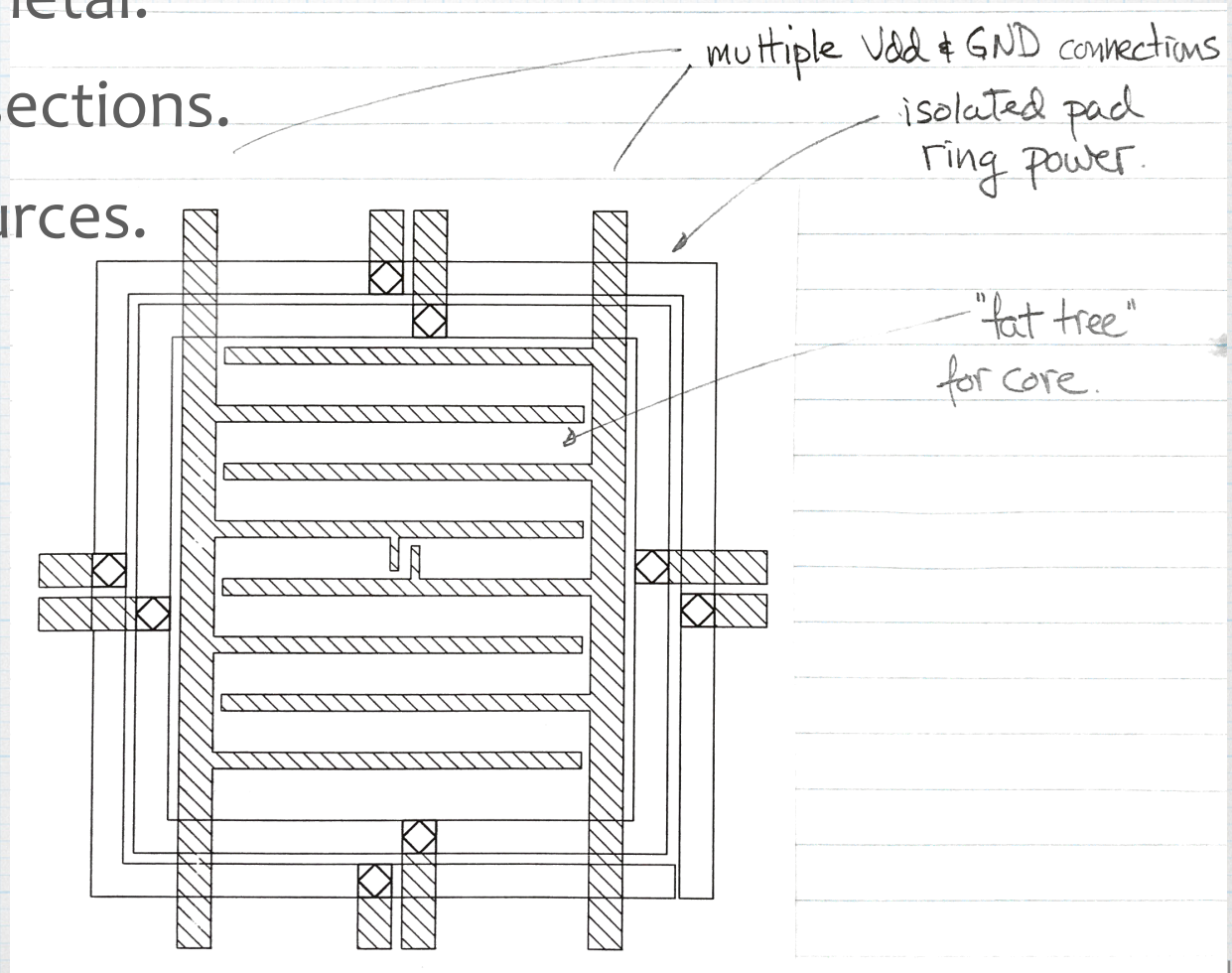- For $\Delta V_{dd,max}$ = 100mV, $Z_{dd,max}$ = 100mV/100A = 1mΩ!

IR Drop Example

▸ Intel Pentium 4: ~103W at ~1.275V

I_{dd} = 81Amps

▸ For 10% IR drop, total distribution resistance must be less than 1.6mΩ

▸ On-chip wire R ≈ 20mΩ/sq. (thick metal)

  ▸ Can't meet R requirement even with multiple, complete layers dedicated to power

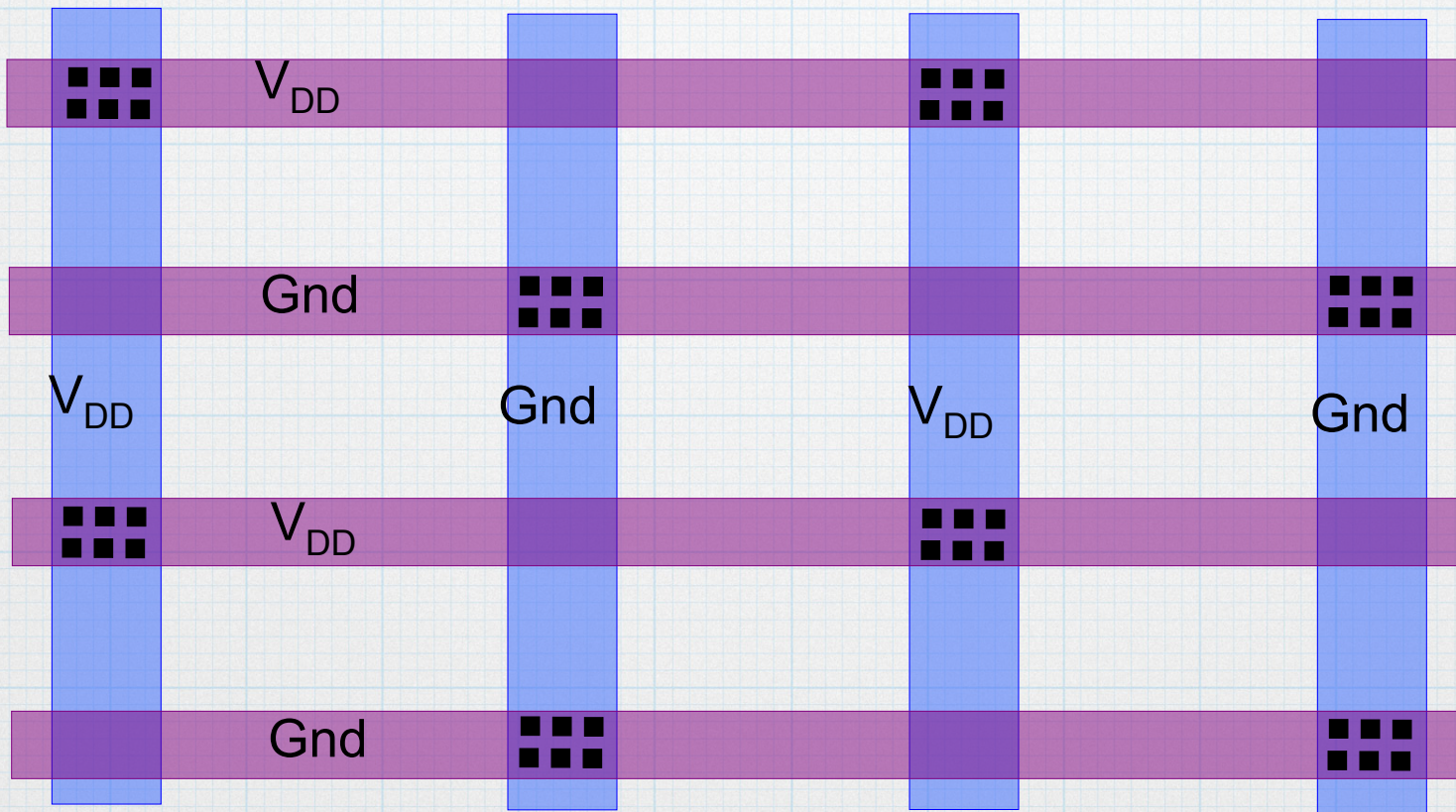 ▸ Main motivation for flip-chip packaging

Layout Strategy

1. Keep distance form source of power/gnd as short as possible.

2. Use wide thick metal.

3. Isolate "noisy" sections.

4. Use multiple sources.

multiple Vdd & GND connections

isolated pad ring power.

"fat tree" for core.

Popular On-Chip Power

▸ Power network usually follows pre-defined template (often referred to as "power grid")
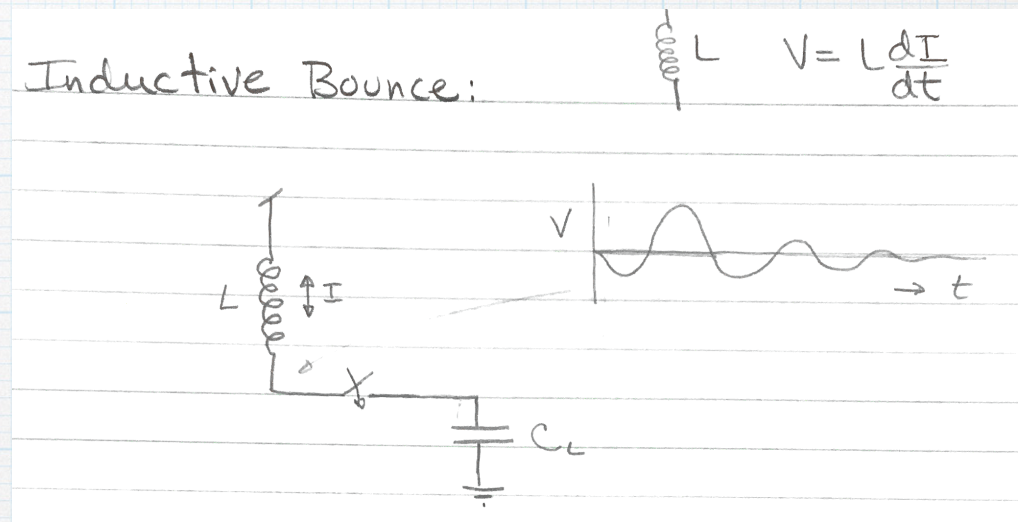
Inductive Bounce

Inductance in the power & ground paths results in voltage glitches (noise) on the Vdd & GND nodes.

On chip L value of wires is small => usually not significant except:

1. Very large currents: clock drivers, off-chip drivers

2. Package pins, bonding wires (1nH/mm)

Inductive Bounce:
L $V = L\dfrac{dI}{dt}$

Package pins can have from 2 - 40nH of inductance, depending on package type
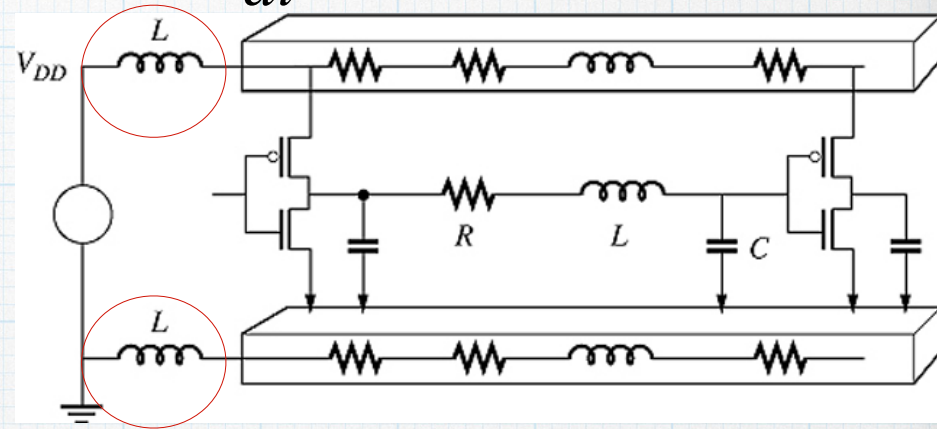
Strategy:

1. Use multiple bonding pads (wiress) for Vdd and GND

2. Use on -chip by pass capacitors

Pin Inductance

$$V = L \cdot \frac{dI}{dt}$$

▸ Major source of inductance is through the bonding pin connections to the chip package.

▸ C4 bump inductance is 25pH
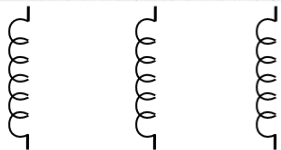
▸ wire-bond inductance of 1nH/mm

❑ Example:

  ❑ Processor transient current is 50A in 20ps from 1V supply

  ❑ How many C4 bumps do we need to get supply noise spike of less than 10%?

  ❑ With wirebonds, how many wirebonds are needed?

Pin Inductance Example

▸ Processor transient current is 50A in 20ps from 1V supply:

$$V = L \cdot \frac{dI}{dt} \qquad L = V \cdot \frac{dt}{dI} = 0.1V \cdot \frac{20ps}{50A} = 0.04pH$$

▸ C4 bump inductance is 25pH

▸ How many C4 bumps do we need to get supply noise spike of less than 10%?
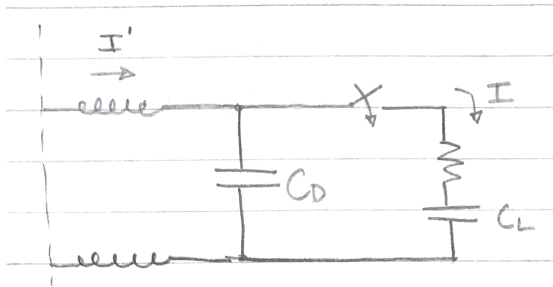
Inductors in parallel 1/add
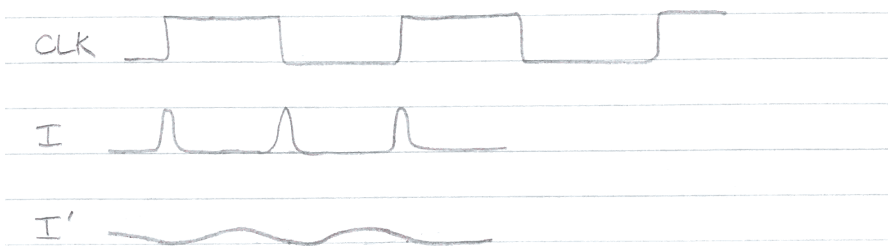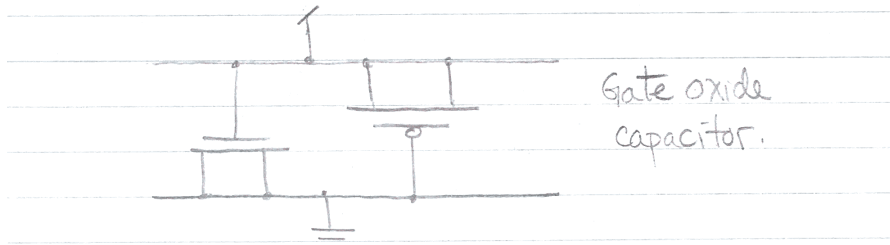
$$\frac{25pH}{0.04pH} = 625$$

$$\frac{1000pH}{0.04pH} > 25K!$$

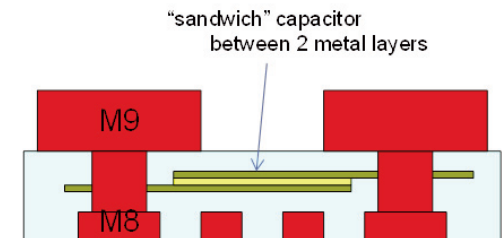# On-chip Decoupling Capacitors Help with Inductive and Resistive Effects

▸ When transistors switch - current is drawn from C_D rather than through package pins and bonding wires - smooths our dI/dt.

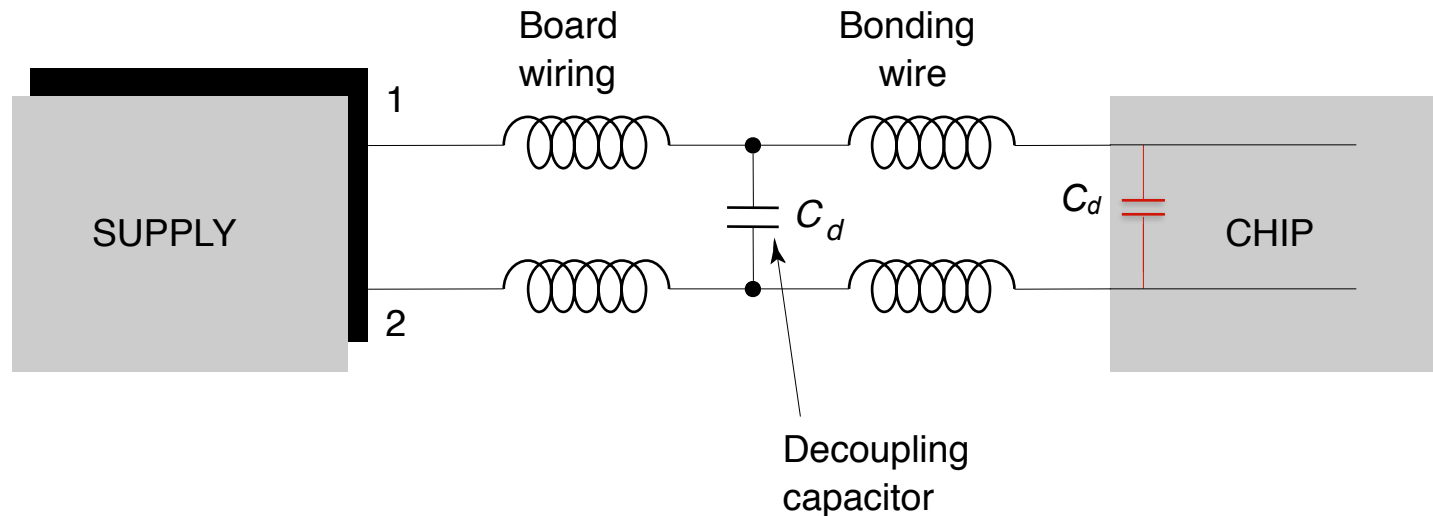▸ Distributed bypass capacitors also smooth out noise from IR drops.

MIM Cap :density (20-30 ff/um^2)

"sandwich" capacitor between 2 metal layers

M9

M8

Decap cell in stdcell library added by tools.

Decoupling Capacitors On-chip and on-board

Decoupling capacitors are added:

- On the board (right under the supply pins)
- On the chip (under the supply straps, near large buffers)
- C_d helps avoid current rushing through supply wires
  - local store of charge
  - "smoothing filter" on supply voltage

Decoupling Capacitors

▸ Under the die